

SCHOTTKY BARRIER DIODE**Features**

- Low VF
- Super high speed switching.
- High reliability by planer design.

Applications

- High speed power switching.

Maximum Ratings and Characteristics

- Absolute Maximum Ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}		20	V
Repetitive peak surge reverse voltage	V_{RSM}	$t_w=500\text{ns}, \text{duty}=1/40$	20	V
Isolating voltage	V_{iso}	Terminals to Case, AC. 1min.	1500	V
Average output current	I_o	duty=1/2, $T_c=94^\circ\text{C}$ Square wave	16*	A
Surge current	I_{FSM}	Sine wave 10ms	120	A
Operating junction temperature	T_j		+150	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to +150	$^\circ\text{C}$

* Out put current of centertap full wave connection.

- Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Conditions	Max.	Unit
Forward voltage drop **	V_F	$I_F=4.0\text{A}$	0.39	V
Reverse current **	I_R	$V_R=V_{RRM}$	10.0	mA
Thermal resistance	$R_{th(j-c)}$	Junction to case	3.5	$^\circ\text{C/W}$

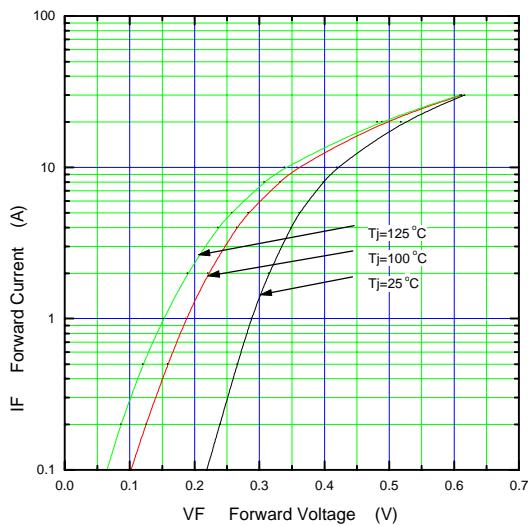
** Rating per element

- Mechanical Characteristics

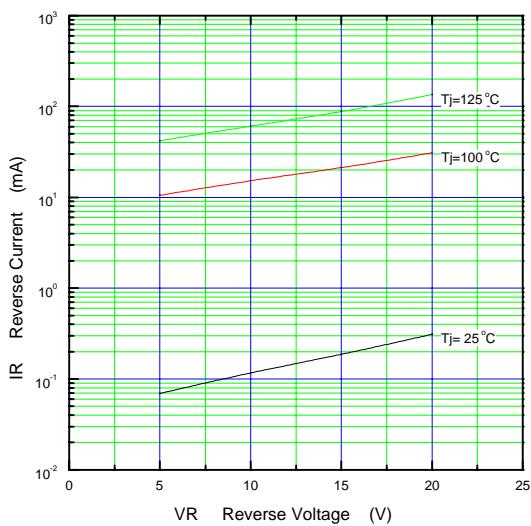
Mounting torque	Recommended torque	0.3 to 0.5	$\text{N} \cdot \text{m}$
Weight		2.3	g

■ Characteristics

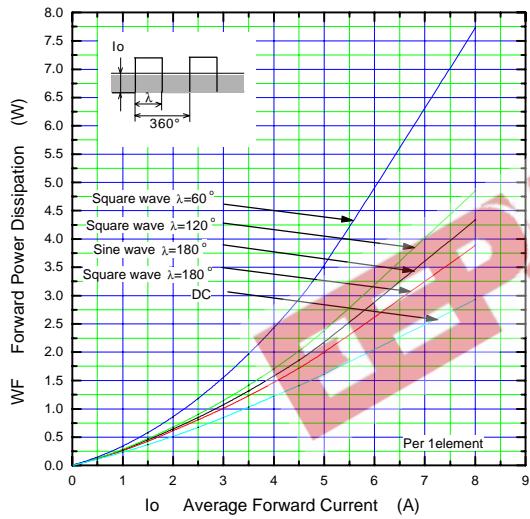
Forward Characteristic (typ.)



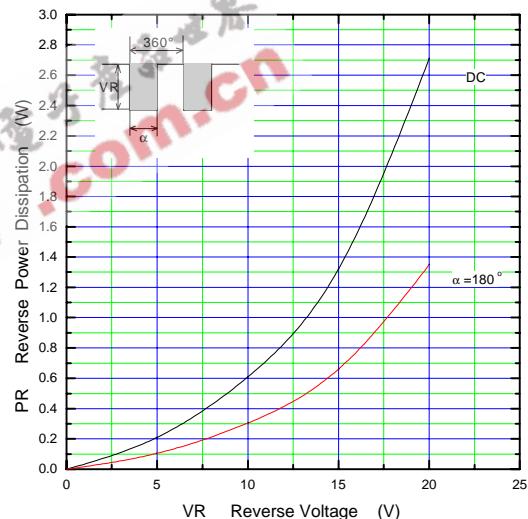
Reverse Characteristic (typ.)



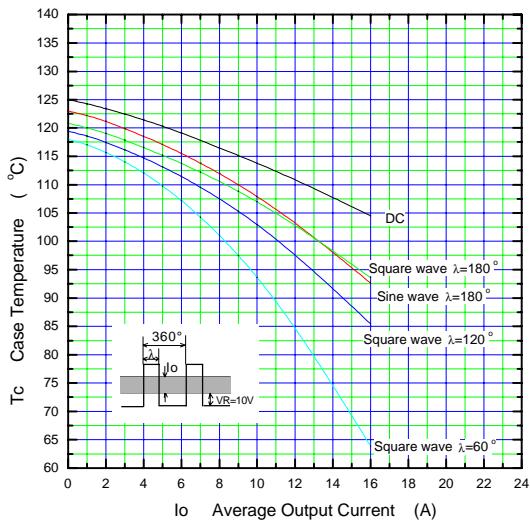
Forward Power Dissipation



Reverse Power Dissipation



Current Derating (Io-Tc)



λ : Conduction angle of forward current for each rectifier element
 Io : Output current of center-tap full wave connection

Junction Capacitance Characteristic (typ.)

